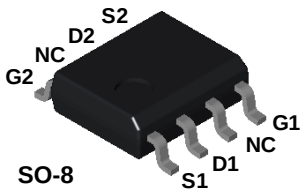
Index of /ds/NP/

Name	Last modified	Size	Description
Parent Directory			
NPDS402.pdf	22-Dec-99 00:13	123K	
NPDS403.pdf	22-Dec-99 00:13	123K	
NPDS404.pdf	22-Dec-99 00:13	123K	
NPDS405.pdf	22-Dec-99 00:13	123K	
NPDS5565.pdf	22-Dec-99 00:13	130K	
NPDS5566.pdf	22-Dec-99 00:13	130K	
NPDS5911.pdf	22-Dec-99 00:13	121K	
NPDS5912.pdf	22-Dec-99 00:13	121K	
NPDS8301.pdf	22-Dec-99 00:13	109K	
NPDS8302.pdf	22-Dec-99 00:13	109K	
NPDS8303.pdf	22-Dec-99 00:13	109K	
NPN_Epitaxial_Silicon+	16-Apr-99 13:01	73K	

FAIRCHILD SEMICONDUCTOR™

Discrete POWER & Signal Technologies

NPDS402
NPDS403
NPDS404
NPDS406



N-Channel General Purpose Dual Amplifier

Sourced from Process 98.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{DG}	Drain-Gate Voltage	50	V
V_{GS}	Gate-Source Voltage	50	V
I_{GF}	Forward Gate Current	10	mA
T_J , T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:
1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

General Purpose Dual Amplifier
(continued)

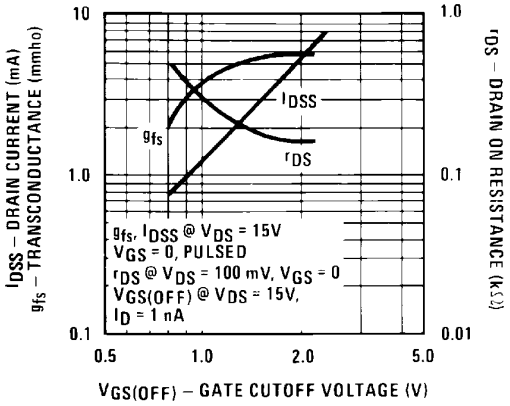
Electrical Characteristics
TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHARACTERISTICS					
$V_{(BR)GSS}$	Gate-Source Breakdown Voltage	I_G = 1.0 µA, V_{DS} = 0	- 50		V
I_{GSS}	Gate Reverse Current	V_{GS} = 30 V, V_{DS} = 0		25	pA
$V_{GS(off)}$	Gate-Source Cutoff Voltage	V_{DS} = 15 V, I_D = 1.0 nA	- 0.5	- 2.5	V
V_{GS}	Gate-Source Voltage	V_{DG} = 15 V, I_D = 200 µA		- 2.3	V
$V_{G1 - G2}$	Voltage Gate 1-Gate 2	I_G = 1.0 µA, V_{DS} = 0	+ / - 50		V
ON CHARACTERISTICS					
I_{DSS}	Zero-Gate Voltage Drain Current*	V_{DS} = 10 V, V_{GS} = 0	0.5	10	mA
SMALL SIGNAL CHARACTERISTICS					
g_{fs}	Common Source Forward Transconductance	V_{DS} = 10 V, V_{GS} = 0, f = 1.0 kHz V_{DS} = 15 V, I_D = 200µA, f = 1.0 kHz	2000 1000	7000 2000	µmhos µmhos
g_{oss}	Common Source Output Conductance	V_{DS} = 10 V, V_{GS} = 0, f = 1.0 kHz		20	µmhos
g_{os}	Common Source Output Conductance	V_{DS} = 15 V, I_D = 200µA, f = 1.0 kHz		2.0	µmhos
C_{iss}	Input Capacitance	V_{DG} = 15 V, I_D = 200 µA, f = 1.0 MHz		8.0	pF
C_{rss}	Reverse Transfer Capacitance	V_{DG} = 15 V, I_D = 200 µA, f = 1.0 MHz		3.0	pF
CMMR	Common Mode Rejection	V_{DG} = 10 to 20 V, I_D = 200 µA	95		dB
$V_{GS1} - V_{GS2}$	Differential Match	V_{DG} = 10 V, I_D = 200 µA, **NPDS402** **NPDS403** **NPDS404** **NPDS406**		 10 10 15 40	 mV mV mV mV
$\Delta V_{GS1} - V_{GS2}$	Differential Drift	V_{DG} = 10 V, I_D = 200 µA, T_A = -55 to 25 °C **NPDS402** **NPDS403** **NPDS404** **NPDS406** V_{DG} = 10 V, I_D = 200 µA T_A = 25 to 125 °C **NPDS402** **NPDS403** **NPDS404** **NPDS406**		 10 25 25 80 10 25 25 80	 µV/°C µV/°C µV/°C µV/°C µV/°C µV/°C µV/°C µV/°C

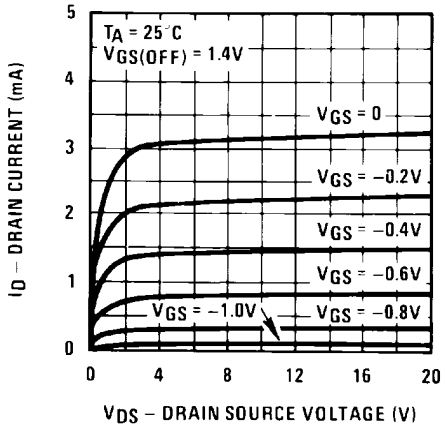
*Pulse Test: Pulse Width ≤ 300 ms, Duty Cycle ≤ 2%

Typical Characteristics (continued)

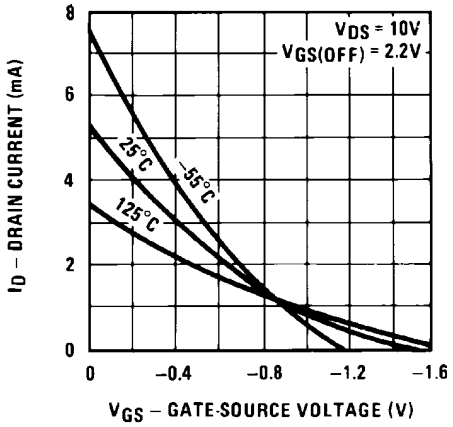
Parameter Interactions



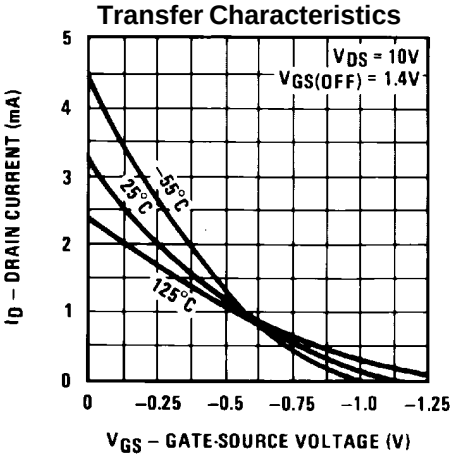
Common Drain-Source



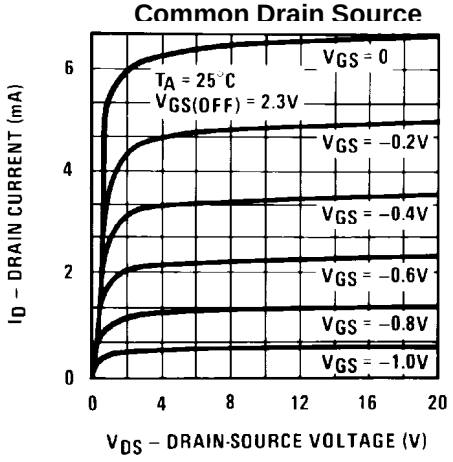
Transfer Characteristics



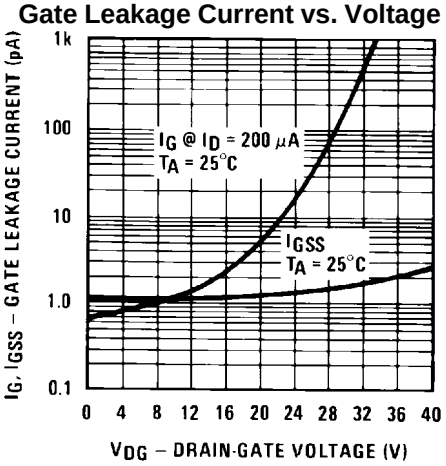
Transfer Characteristics



Common Drain Source

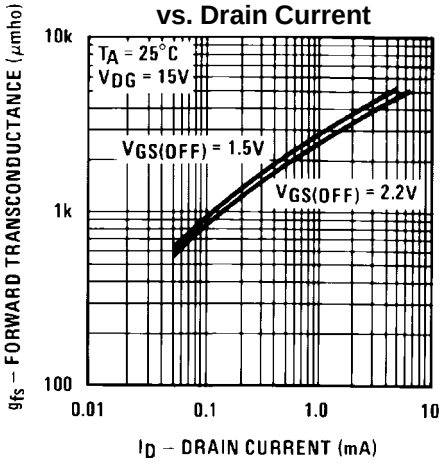


Gate Leakage Current vs. Voltage

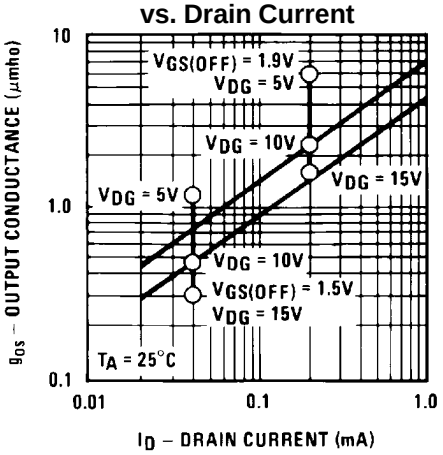


Typical Characteristics (continued)

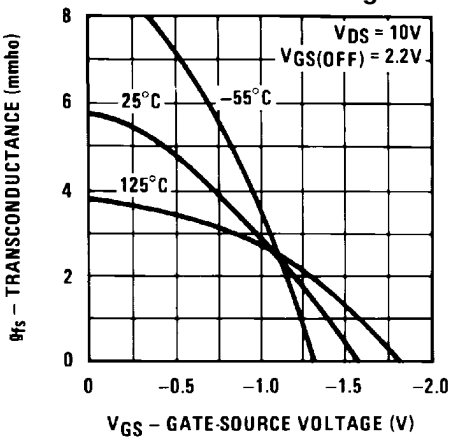
Forward Transconductance vs. Drain Current



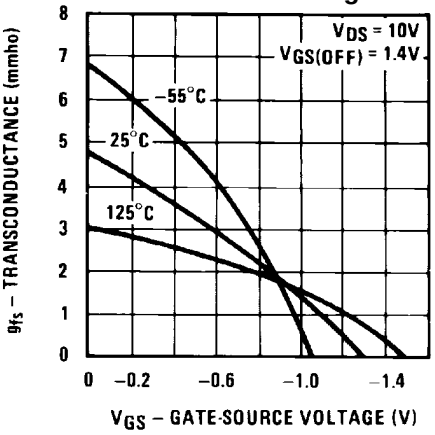
Output Conductance vs. Drain Current



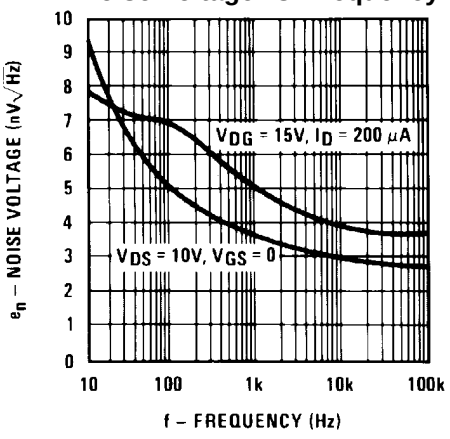
Transconductance vs. Gate Source Voltage



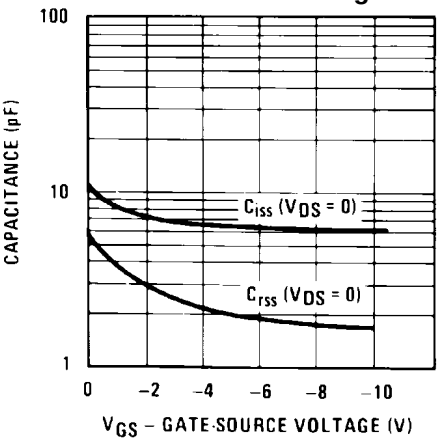
Transconductance vs. Gate Source Voltage



Noise Voltage vs. Frequency

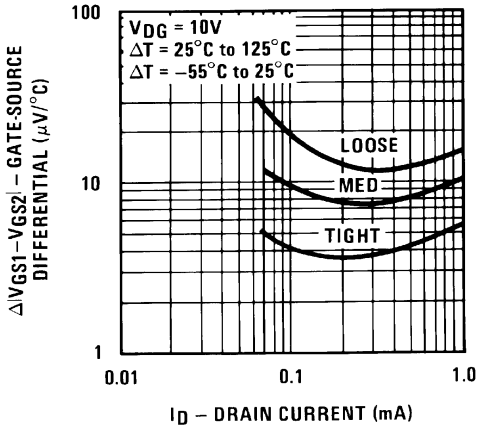


Capacitance vs. Gate Source Voltage

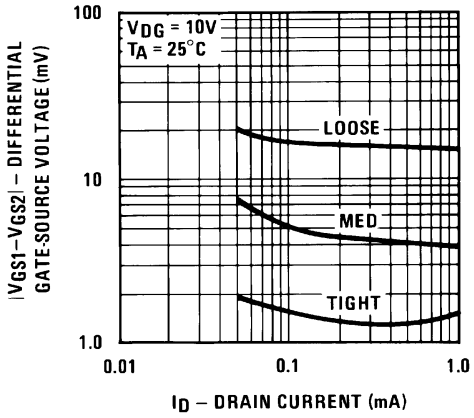


Typical Characteristics (continued)

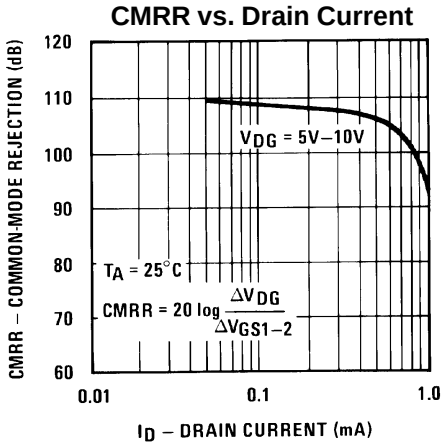
Differential Drift



Differential Offset



CMRR vs. Drain Current



FAIRCHILD SEMICONDUCTOR™

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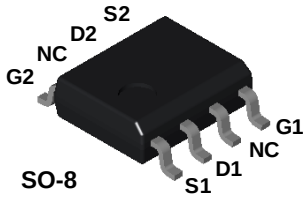
NPDS5565
NPDS5566



N-Channel General Purpose Dual Amplifier

Sourced from Process 96.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{DG}	Drain-Gate Voltage	40	V
V_{GS}	Gate-Source Voltage	40	V
I_{GF}	Gate Current	10	mA
T_J ,T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:
1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

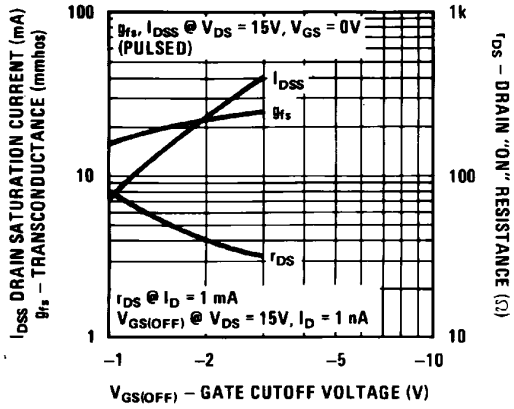
General Purpose Dual Amplifier
(continued)

Electrical Characteristics
TA = 25°C unless otherwise noted

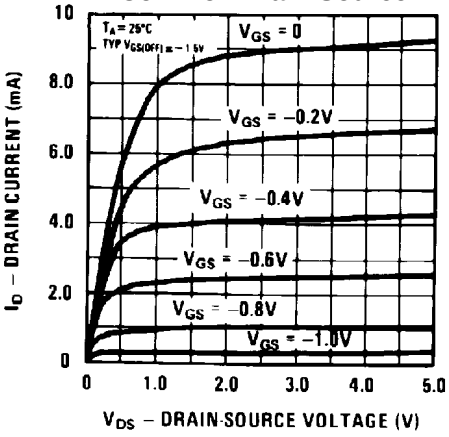
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHARACTERISTICS					
$V_{(BR)GSS}$	Gate-Source Breakdown Voltage	I_G = 1.0 µA, V_{DS} = 0	- 40		V
I_{GSS}	Gate Reverse Current	V_{GS} = 20 V, V_{DS} = 0 V_{GS} = 20 V, V_{DS} = 0, T_A = 150 °C		100 200	pA µA
$V_{GS(off)}$	Gate-Source Cutoff Voltage	V_{DS} = 15 V, I_D = 1.0 nA	- 0.5	- 3.0	V
$V_{GS(f)}$	Forward Gate-Source Voltage	V_{DS} = 0, I_D = 2.0 mA		1.0	V
$V_{G1 - G2}$	Voltage Gate 1 - Gate 2	V_{DS} = 0, I_G = + / - 1.0 µA	+ / - 40		V
ON CHARACTERISTICS					
I_{DSS}	Zero-Gate Voltage Drain Current*	V_{DS} = 15 V, V_{GS} = 0	5.0	30	mA
$r_{DS(on)}$	Drain-Source On Resistance	I_D = 1.0 mA, V_{GS} = 0		100	Ω
SMALL SIGNAL CHARACTERISTICS					
g_{fs}	Common Source Forward Transconductance	V_{DS} = 15 V, I_D = 2.0mA, f = 1.0 kHz V_{DS} = 15 V, I_D = 2.0 mA, f = 100 MHz	7500 7000	12,500	µmhos µmhos
g_{oss}	Common Source Output Conductance	V_{DS} = 15 V, I_D = 2.0mA, f = 1.0 kHz		45	µmhos
C_{iss}	Input Capacitance	V_{DG} = 15 V, I_D = 2.0mA, f = 1.0MHz		12	pF
C_{rss}	Reverse Transfer Capacitance	V_{DS} = 15 V, I_D = 2.0mA, f = 1.0 kHz		3.0	pF
e_n	Equivalent Short-Circuit Input Noise Voltage	V_{DG} = 15 V, I_D = 2.0 mA, f = 10 Hz		50	nV/√Hz
NF	Noise Figure	V_{DG} = 15 V, I_D = 2.0 mA, f = 10 Hz R_G = 1.0 mΩ		1.0	dB
I_{DSS1} - I_{DSS2}	I_{DSS} Match	V_{DS} = 15 V, V_{GS} = 0		5.0	%
g_{fs1} - g_{fs2}	g_{fs} Match	V_{DS} = 15 V, I_D = 2.0mA, f = 1.0 kHz		10	%
V_{GS1} - V_{GS2}	Differential Match	V_{DG} = 15 V, I_D = 2.0 mA, **NPDS5565** **NPDS5566**		 10 20	 mV mV
ΔV_{GS1} - V_{GS2}	Differential Drift	V_{DS} = 10 V, V_{GS} = 0, f = 1.0 kHz T_A = 25 to 125 °C **NPDS5565** **NPDS5566** V_{DG} = 15 V, I_D = 2.0 mA, T_A = -55 to 25 °C **NPDS5565** **NPDS5566**		 25 50 25 50	 µV/°C µV/°C µV/°C µV/°C

Typical Characteristics (continued)

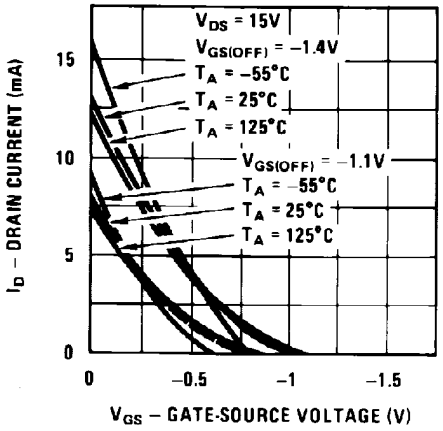
Parameter Interactions



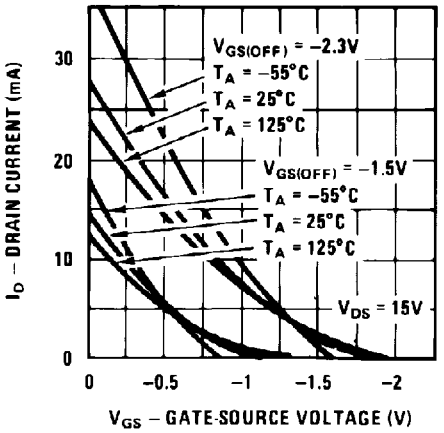
Common Drain-Source



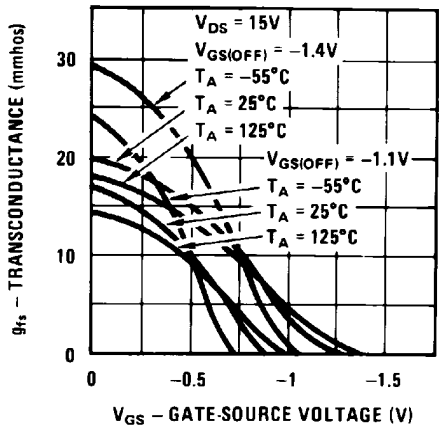
Transfer Characteristics



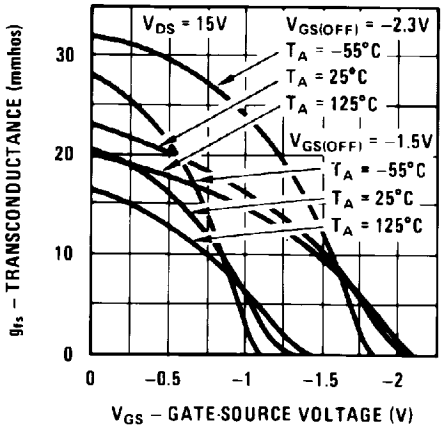
Transfer Characteristics



Transfer Characteristics

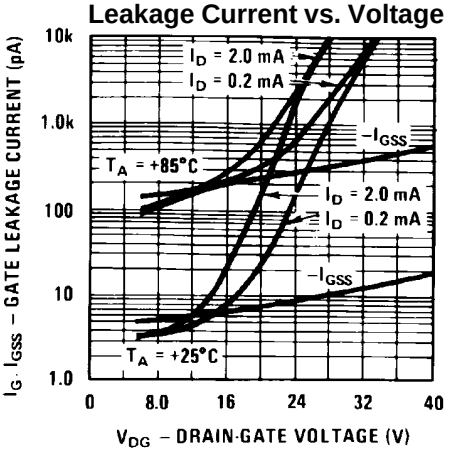


Transfer Characteristics

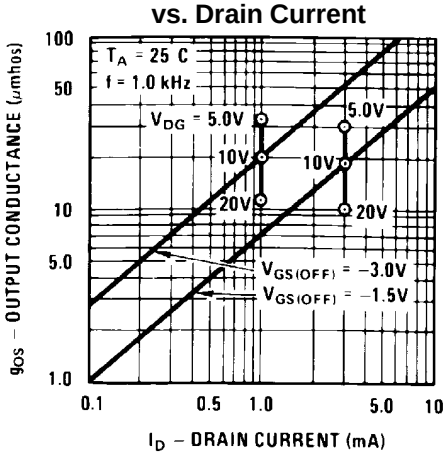


Typical Characteristics (continued)

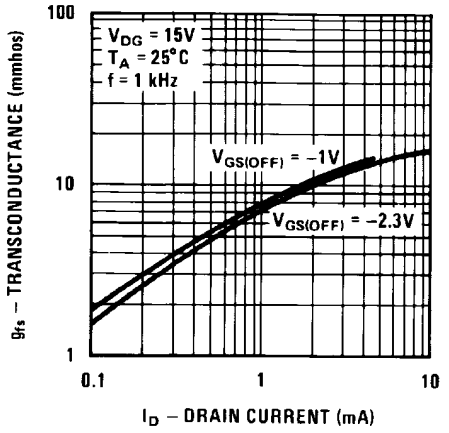
Leakage Current vs. Voltage



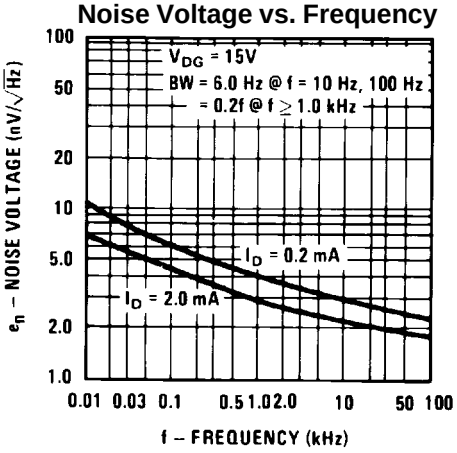
Output Conductance vs. Drain Current



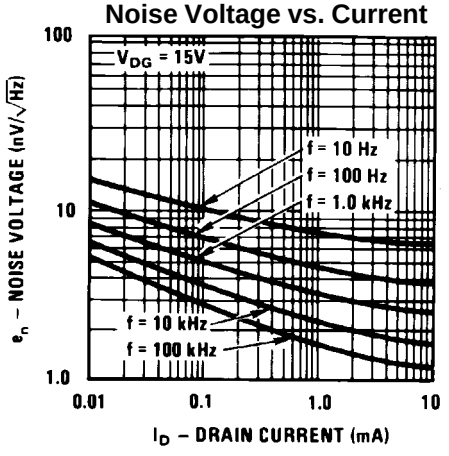
Transconductance vs. Drain Current



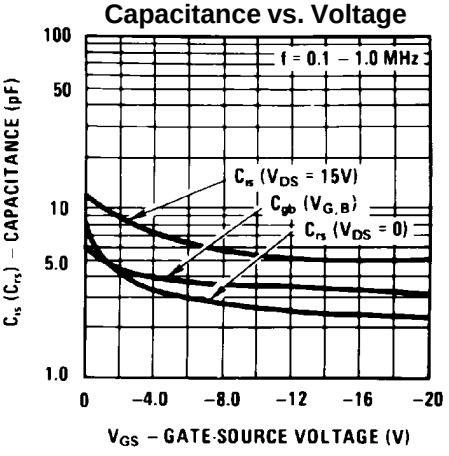
Noise Voltage vs. Frequency



Noise Voltage vs. Current

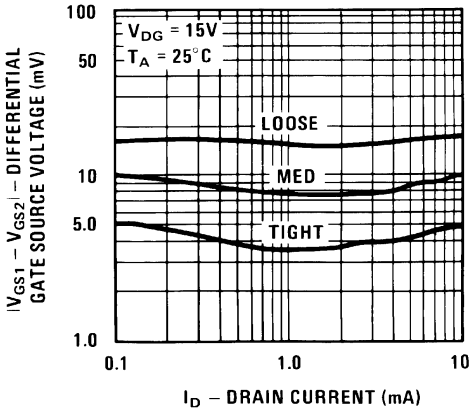


Capacitance vs. Voltage

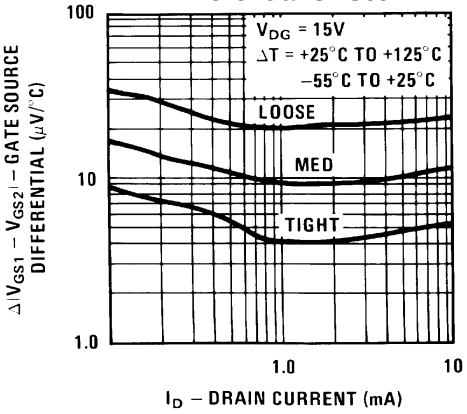


Typical Characteristics (continued)

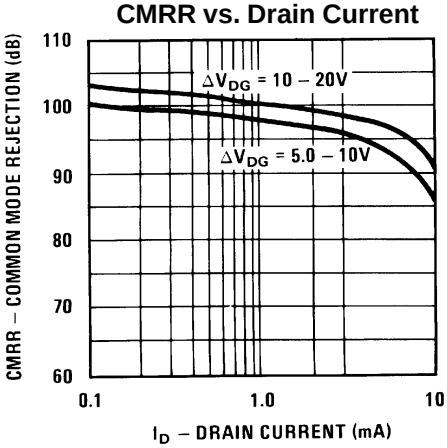
Differential Drift



Differential Offset



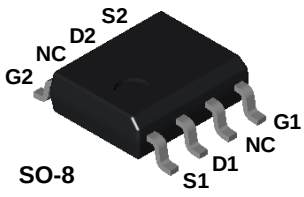
CMRR vs. Drain Current



FAIRCHILD SEMICONDUCTOR TM

Discrete POWER & Signal Technologies

NPDS5911
NPDS5912



N-Channel General Purpose Dual Amplifier

Sourced from Process 93.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{DG}	Drain-Gate Voltage	25	V
V_{GS}	Gate-Source Voltage	25	V
I_{GF}	Forward Gate Current	10	mA
T_J ,T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:
1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

General Purpose Dual Amplifier
(continued)

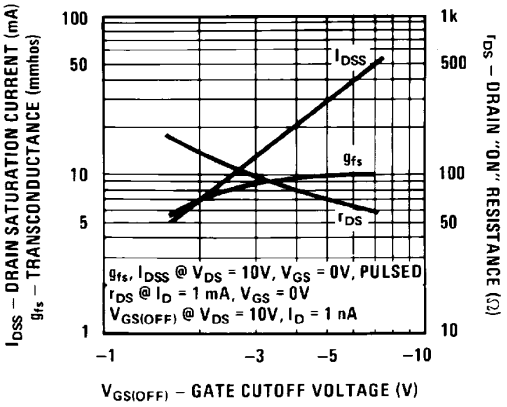
Electrical Characteristics
TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHARACTERISTICS					
$V_{(BR)GSS}$	Gate-Source Breakdown Voltage	I_G = 1.0 µA, V_{DS} = 0	- 25		V
I_{GSS}	Gate Reverse Current	V_{GS} = 15 V, V_{DS} = 0 V_{GS} = 15 V, V_{DS} = 0, T_A = 150 °C		100 250	pA nA
$V_{GS(off)}$	Gate-Source Cutoff Voltage	V_{DS} = 10 V, I_D = 1.0 nA	- 1.0	- 5.0	V
V_{GS}	Gate-Source Voltage	V_{DG} = 10 V, I_D = 5.0 mA	- 0.3	- 4.0	V
$V_{G1 - G2}$	Voltage Gate 1 - Gate 2	V_{DS} = 0, I_G = + / - 1.0 µA	+ / - 25		V
ON CHARACTERISTICS					
I_{DSS}	Zero-Gate Voltage Drain Current*	V_{DS} = 10 V, V_{GS} = 0	7.0	40	mA
SMALL SIGNAL CHARACTERISTICS					
g_{fs}	Common Source Forward Transconductance	V_{DS} = 10 V, I_D = 5.0mA, f = 1.0 kHz V_{DS} = 10 V, I_D = 5.0 mA, f = 100 MHz	5000 5000	10,000 10,000	µmhos µmhos
g_{oss}	Common Source Output Conductance	V_{DS} = 10 V, I_D = 5.0mA, f = 1.0 kHz V_{DS} = 10V, I_D = 5.0mA, f = 100 MHz		100 150	µmhos µmhos
C_{iss}	Input Capacitance	V_{DG} = 10 V, I_D = 5.0mA, f =1.0 MHz		5.0	pF
C_{rss}	Reverse Transfer Capacitance	V_{DS} = 10 V, I_D = 5.0mA, f = 1.0 kHz		1.2	pF
e_n	Equivalent Short-Circuit Input Noise Voltage	V_{DG} = 10 V, I_D = 5.0 mA, f = 10 kHz		20	nV/√Hz
NF	Noise Figure	V_{DG} = 10 V, I_D = 5.0 mA, f = 10 kHz R_G = 100 kΩ		1.0	dB
I_{DSS1} -I_{DSS2}	I_{DSS} Match	V_{DS} = 10 V, V_{GS} = 0		5.0	%
g_{fs1} - g_{fs2}	g_{fs} Match	V_{DS} = 10 V, I_D = 5.0mA, f = 1.0 kHz		5.0	%
g_{oss1} -g_{oss2}	g_{oss} Match	V_{DS} = 10 V, I_D = 5.0mA, f = 1.0 kHz		20	µmhos
I_{G1} - I_{G2}	I_G Match	V_{DS} = 10 V, I_D = 5.0mA, T_A = 125°C		20	nA
V_{GS1} - V_{GS2}	Differential Match	V_{DG} = 10 V, I_D = 5.0 mA, **NPDS5911** **NPDS5912**		 10 15	 mV mV
ΔV_{GS1} - V_{GS2}	Differential Drift	V_{DG} = 10 V, V_{GS} = 0, I_D = 5.0 mA, T_A = 25 to 125 °C **NPDS5911** **NPDS5912** V_{DG} = 10 V, I_D = 5.0 mA, T_A = -55 to 25 °C **NPDS5911** **NPDS5912**		 20 40 20 40	 µV/°C µV/°C µV/°C µV/°C

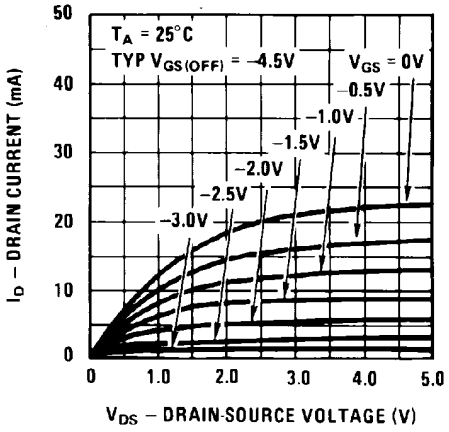
*Pulse Test: Pulse Width ≤ 300 ms, Duty Cycle ≤ 2%

Typical Characteristics (continued)

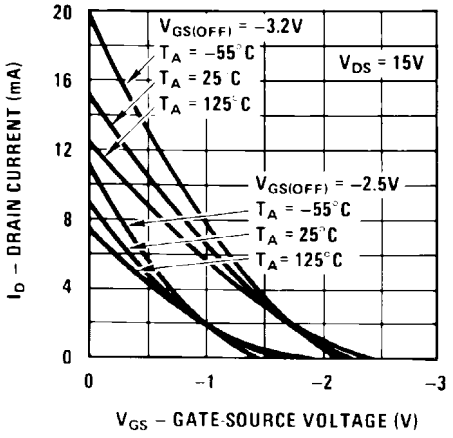
Parameter Interactions



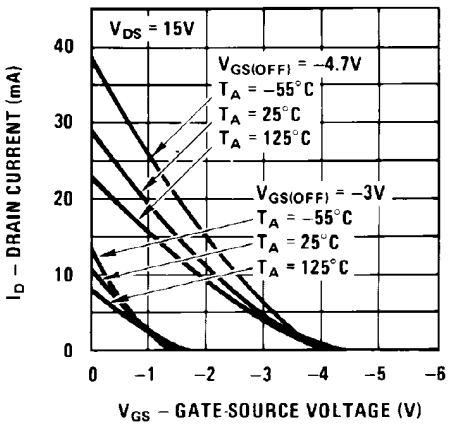
Common Drain-Source



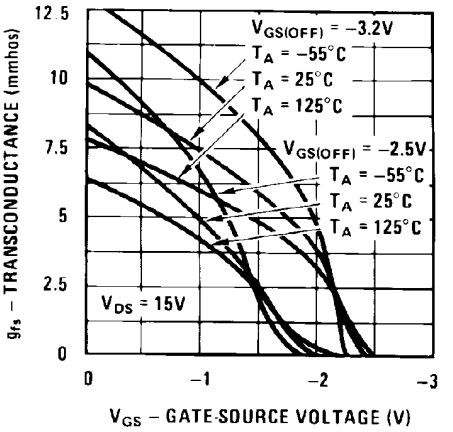
Transfer Characteristics



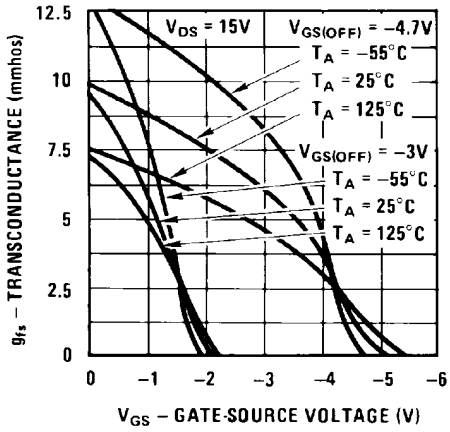
Transfer Characteristics



Transfer Characteristics

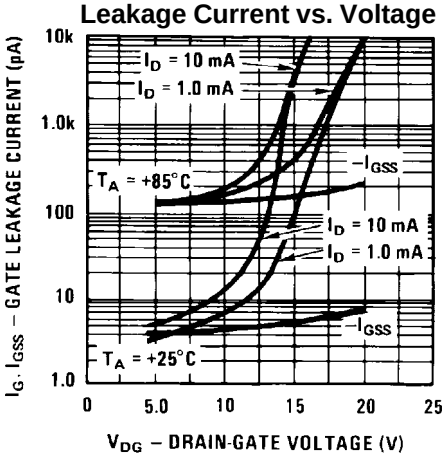


Transfer Characteristics

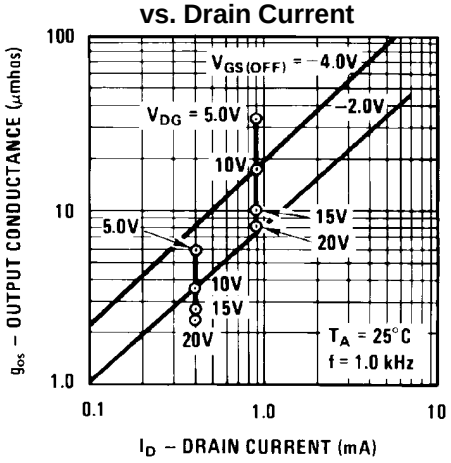


Typical Characteristics (continued)

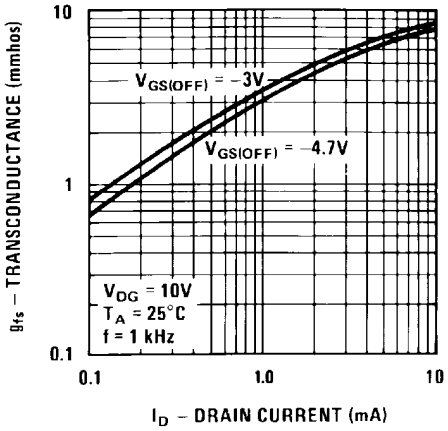
Leakage Current vs. Voltage



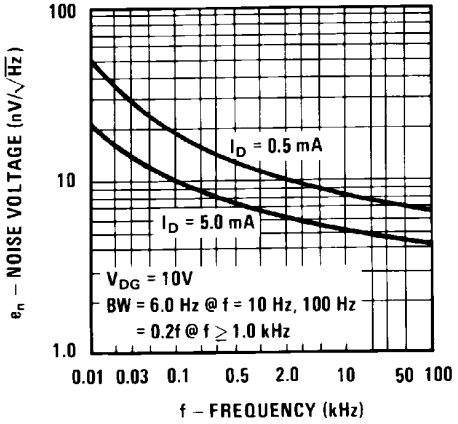
Output Conductance vs. Drain Current



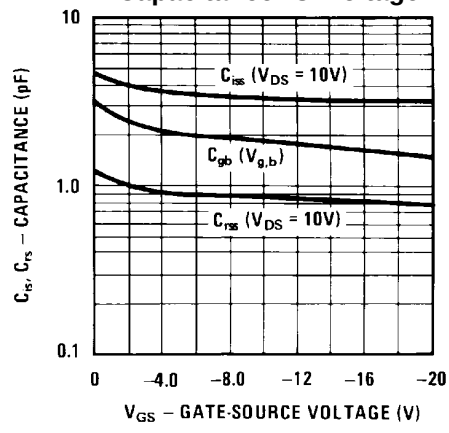
Transconductance vs. Drain Current



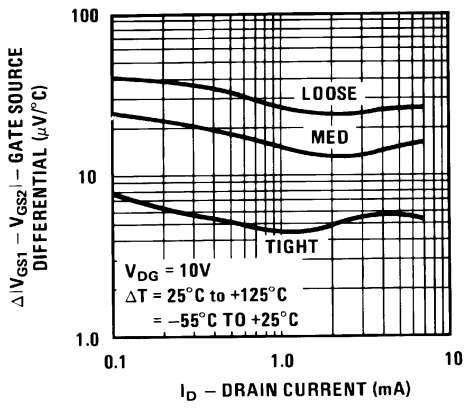
Noise Voltage vs. Frequency



Capacitance vs. Voltage

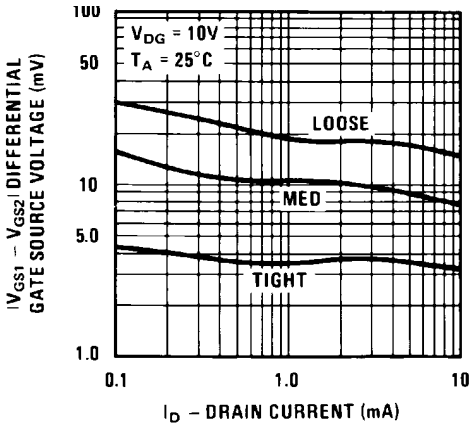


Differential Drift

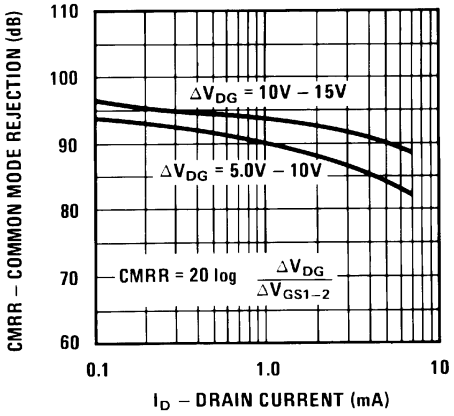


Typical Characteristics (continued)

Differential Offset



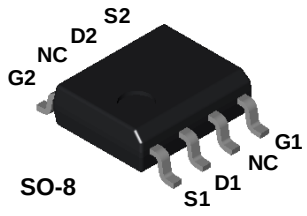
CMRR vs. Drain Current



FAIRCHILD SEMICONDUCTOR TM

Discrete POWER & Signal Technologies

NPDS8301
NPDS8302
NPDS8303



N-Channel General Purpose Dual Amplifier

Sourced from Process 83.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{DG}	Drain-Gate Voltage	40	V
V_{GS}	Gate-Source Voltage	40	V
I_{GF}	Forward Gate Current	10	mA
T_J , T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:
1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

General Purpose Dual Amplifier

(continued)

Electrical Characteristics

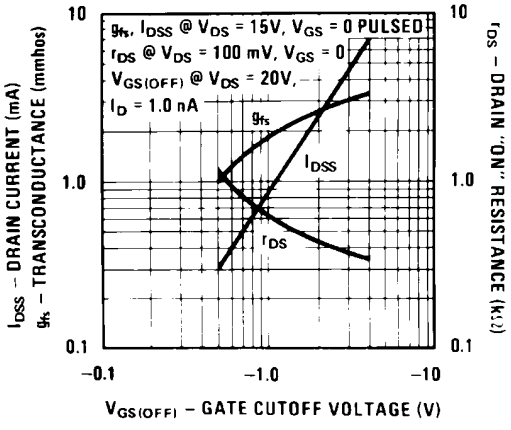
TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHARACTERISTICS					
$V_{(BR)GSS}$	Gate-Source Breakdown Voltage	I_G = 1.0 µA, V_{DS} = 0	- 40		V
I_{GSS}	Gate Reverse Current	V_{GS} = 20 V, V_{DS} = 0		100	pA
$V_{GS(off)}$	Gate-Source Cutoff Voltage	V_{DS} = 20 V, I_D = 1.0 nA	- 0.5	- 3.5	V
V_{GS}	Gate-Source Voltage	V_{DS} = 20 V, I_D = 200 µA	- 0.3	- 3.5	V
ON CHARACTERISTICS					
I_{DSS}	Zero-Gate Voltage Drain Current*	V_{DS} = 20 V, V_{GS} = 0	0.5	6.0	mA
SMALL SIGNAL CHARACTERISTICS					
g_{fs}	Common Source Forward Transconductance	V_{DS} = 20 V, V_{GS} = 0, f = 1.0 kHz V_{DS} = 20 V, I_D = 200 µA, f = 1.0 kHz	1000 700	4000 1200	µmhos µmhos
g_{oss}	Common Source Output Conductance	V_{DS} = 20 V, I_D = 200 µA, f = 1.0 kHz		20	µmhos
g_{os}	Common Source Output Conductance	V_{DS} = 20 V, I_D = 200 µA, f = 1.0 kHz		5.0	µmhos
$V_{GS1} - V_{GS2}$	Differential Match	V_{DG} = 20 V, I_D = 200 µA, **NPDS8301** **NPDS8302** **NPDS8303**		 5.0 10 15	 mV mV mV
$\Delta V_{GS1} - V_{GS2}$	Differential Drift	V_{DS} = 20 V, I_D = 200 µA, T_A = 25 to 85 °C **NPDS8301** **NPDS8302** **NPDS8303**		 10 15 25	 µV/°C µV/°C µV/°C

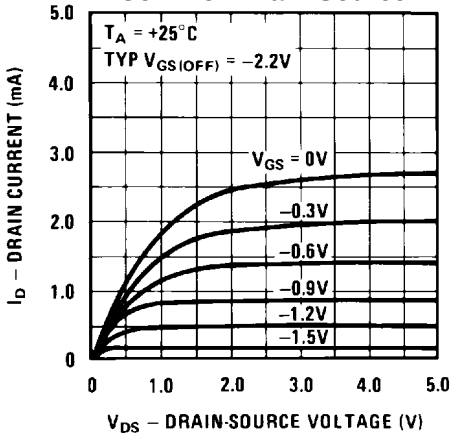
*Pulse Test: Pulse Width ≤ 300 ms, Duty Cycle ≤ 2%

Typical Characteristics

Parameter Interactions

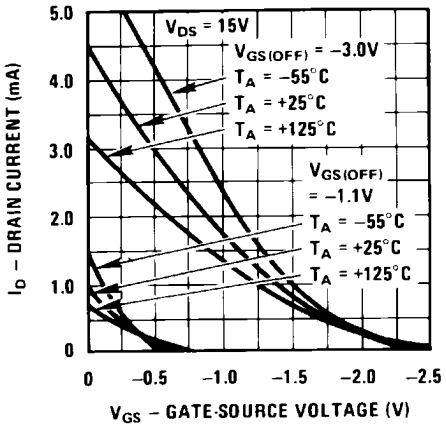


Common Drain-Source

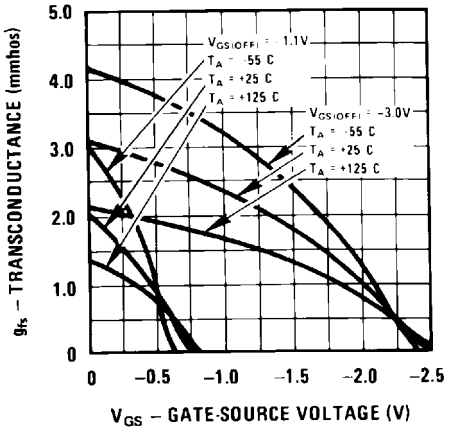


Typical Characteristics (continued)

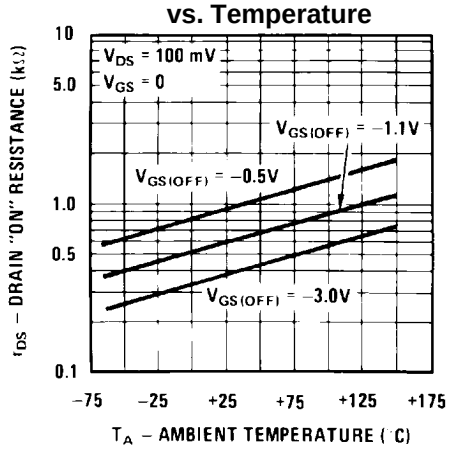
Transfer Characteristics



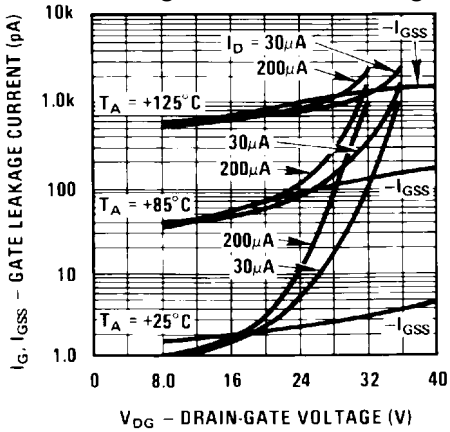
Transfer Characteristics



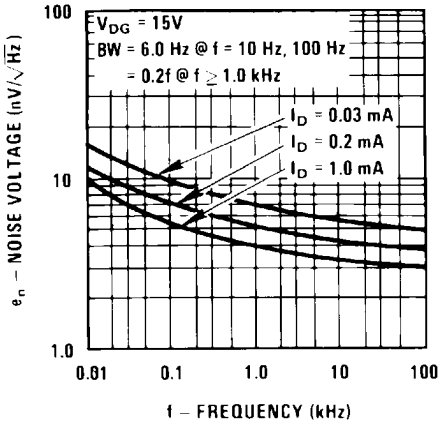
Channel Resistance vs. Temperature



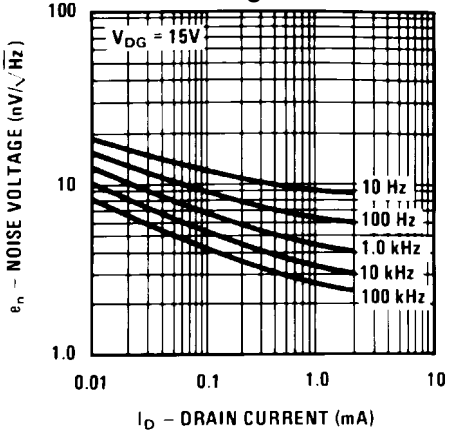
Leakage Current vs. Voltage



Noise Voltage vs. Frequency

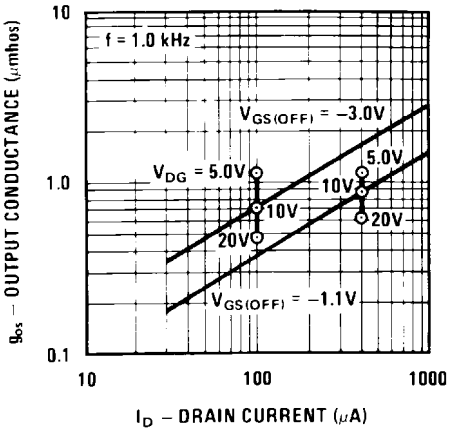


Noise Voltage vs. Current

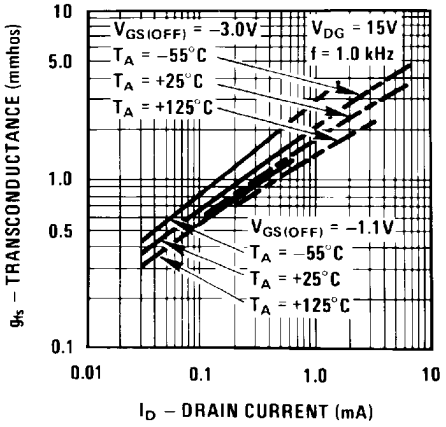


Typical Characteristics (continued)

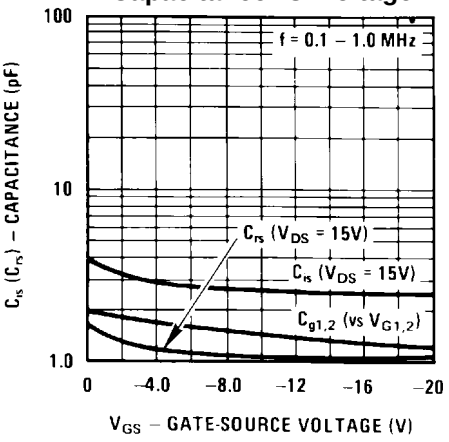
Output Conductance vs. Drain Current



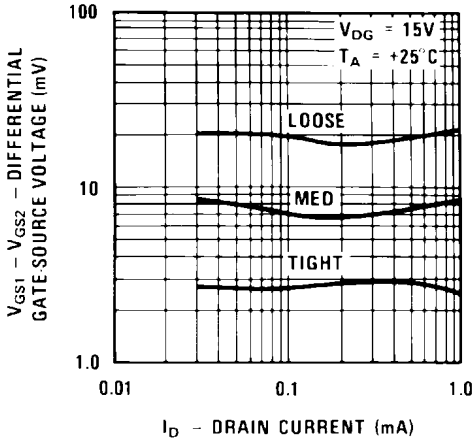
Transconductance vs. Drain Current



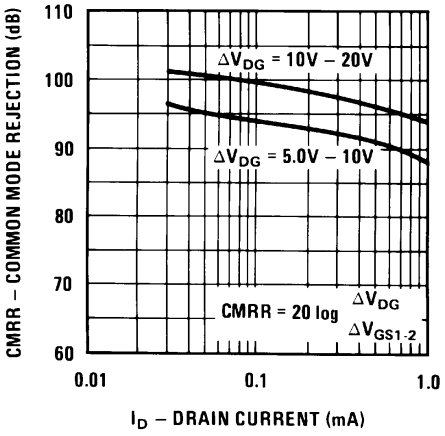
Capacitance vs. Voltage



Differential Offset



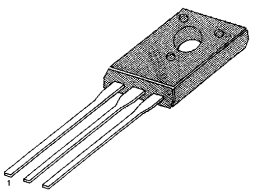
CMRR vs. Drain Current



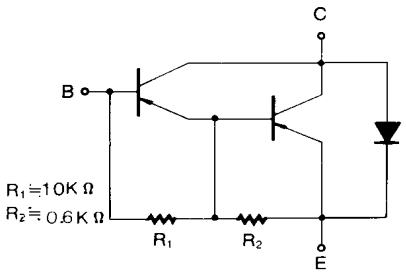
NPN EPITAXIAL
MJE800/801/803 SILICON DARLINGTON TRANSISTOR

HIGH DC CURRENT GAIN
MIN h_{FE}= 750 I $_C$= -1.5 and -2.0A DC
MONOLITHIC CONSTRUCTION WITH
BUILT-IN BASE-EMITTER RESISTORS
• Complement to MJE700/701/702/703

TO-126



1. Emitter 2. Collector 3. Base



ABSOLUTE MAXIMUM RATINGS

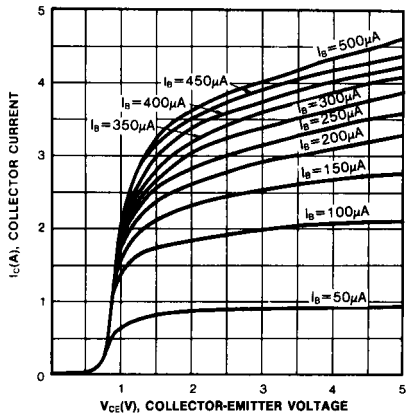
Characteristic	Symbol	Rating	Unit
Collector- Base Voltage	V_{CBO}		
: MJE800/801		60	V
: MJE802/803		80	V
Collector-Emitter Voltage	V_{CEO}		
: MJE800/801		60	V
: MJE802/803		80	V
Emitter- Base Voltage	V_{EBO}	5	V
Collector Current	I_C	4	A
Base Current	I_B	0.1	A
Collector Dissipation (T_C=25°C)	P_C	40	W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55 ~ 150	°C

ELECTRICAL CHARACTERISTICS (T_C=25°C)

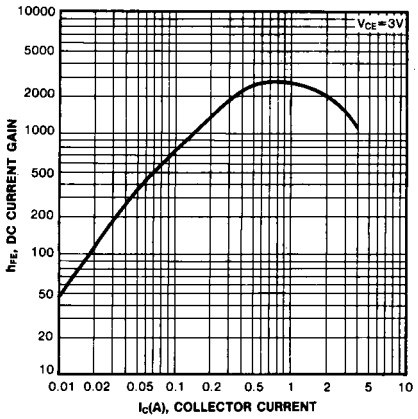
Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Emitter Breakdown Voltage	BV_{CEO}	I_C = 50mA, I_B = 0			
: MJE800/801			60		V
: MJE802/803			80		V
Collector Cutoff Current	I_{CEO}				
: MJE800/801		V_{CE} = 60V, I_B = 0		100	µA
: MJE802/803		V_{CE} = 80V, I_B = 0		100	µA
Collector Cutoff Current	I_{CBO}	V_{CB} = Rated BV_{CEO}, I_E = 0		100	µA
		V_{CB} = Rated BV_{CEO}, I_E = 0 T_C = 100°C		500	µA
Emitter Cutoff Current	I_{EBO}	V_{BE} = 5V, I_C = 0		2	mA
DC Current Gain : MJE800/802	h_{FE}	V_{CE} = 3V, I_C = 1.5A	750		
: MJE801/803		V_{CE} = 3V, I_C = 2A	750		
: ALL DEVICES		V_{CE} = 3V, I_C = 4A	100		
Collector-Emitter Saturation Voltage	V_{CE}(sat)				
: MJE800/802		I_C = 1.5A, I_B = 30mA		2.5	V
: MJE801/803		I_C = 2A, I_B = 40mA		2.8	V
: ALL DEVICES		I_C = 4A, I_B = 40mA		3	V
Base-Emitter On Voltage	V_{BE}(on)				
: MJE800/802		V_{CE} = 3V, I_C = 1.5A		1.2	V
: MJE801/803		V_{CE} = 3V, I_C = 2A		2.5	V
: ALL DEVICES		V_{CE} = 3V, I_C = 4A		3	V

FAIRCHILD SEMICONDUCTOR TM

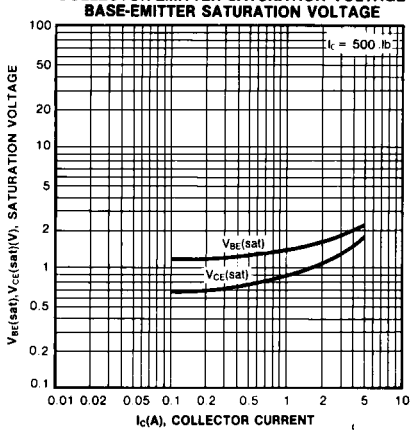
STATIC CHARACTERISTIC



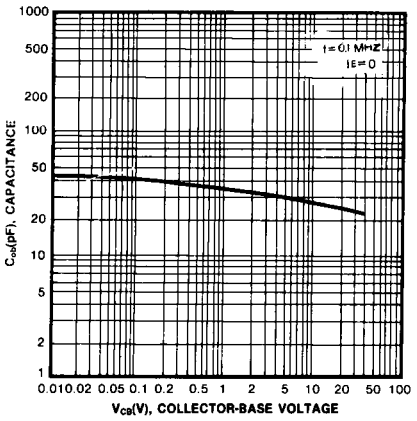
DC CURRENT GAIN



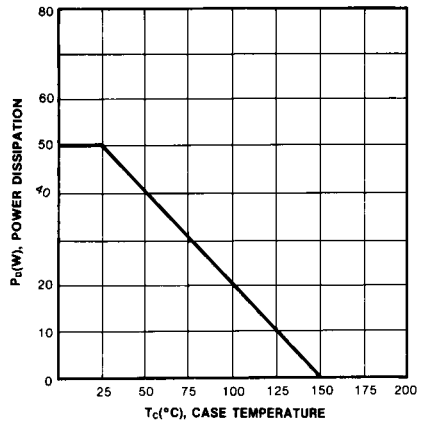
COLLECTOR-EMITTER SATURATION VOLTAGE
BASE-EMITTER SATURATION VOLTAGE



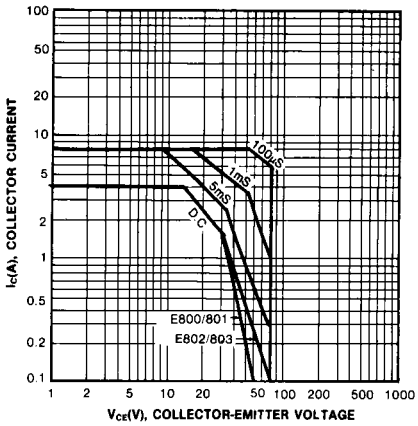
COLLECTOR OUTPUT CAPACITANCE



POWER DERATING



SAFE OPERATING AREA



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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.